

Figure 1. (a) The water layer thickness upon a SiO₂ wafer as 30-minute static water doses occurred in increasing order of pressure with 10-minute Ar purges in between at 75°C/30.4°C reactor/stage. **(b)** The pressure in the chamber during these water doses and purges.

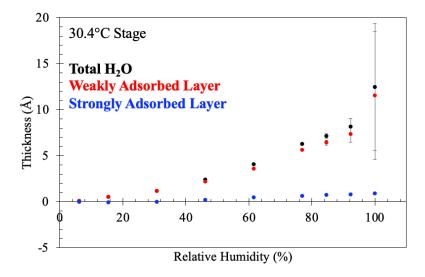


Figure 2. The thickness of the total water layer, weakly adsorbed water layer and strongly adsorbed water layer plotted against relative humidity for the experiment in figure 1.